

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HCT688AP, TC74HCT688AF

8-BIT EQUALITY COMPARATOR

The TC74HCT688A is a high speed CMOS 8-BIT EQUALITY COMPARATOR fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

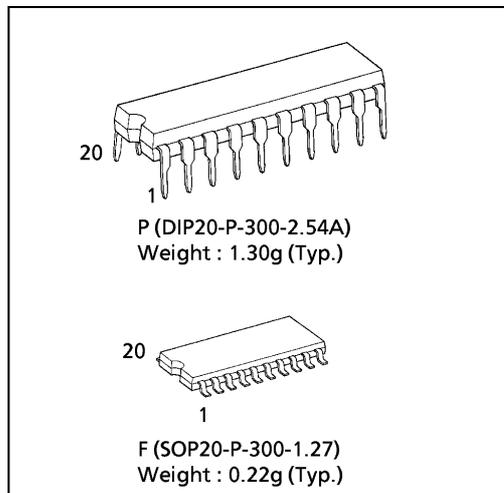
The TC74HCT688A compares two 8-bit binary or BCD words applied inputs P0~P7, and inputs Q0~Q7, and indicates whether or not they are equal.

A signal active low enable is provided to facilitate cascading of several packages to compare of words greater than 8 bits.

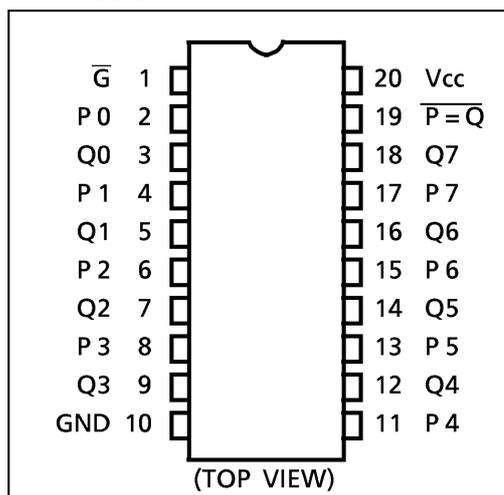
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

- High Speed..... $t_{pd} = 17ns$ (typ.) at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A$ (Max.) at $T_a = 25^\circ C$
- Compatible with TTL outputs..... $V_{IH} = 2.0V$ (Min.)
 $V_{IL} = 0.8V$ (Max.)
- Output Drive Capability..... 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4mA$ (Min.)
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Pin and Function Compatible with 74LS688



PIN ASSIGNMENT



TRUTH TABLE

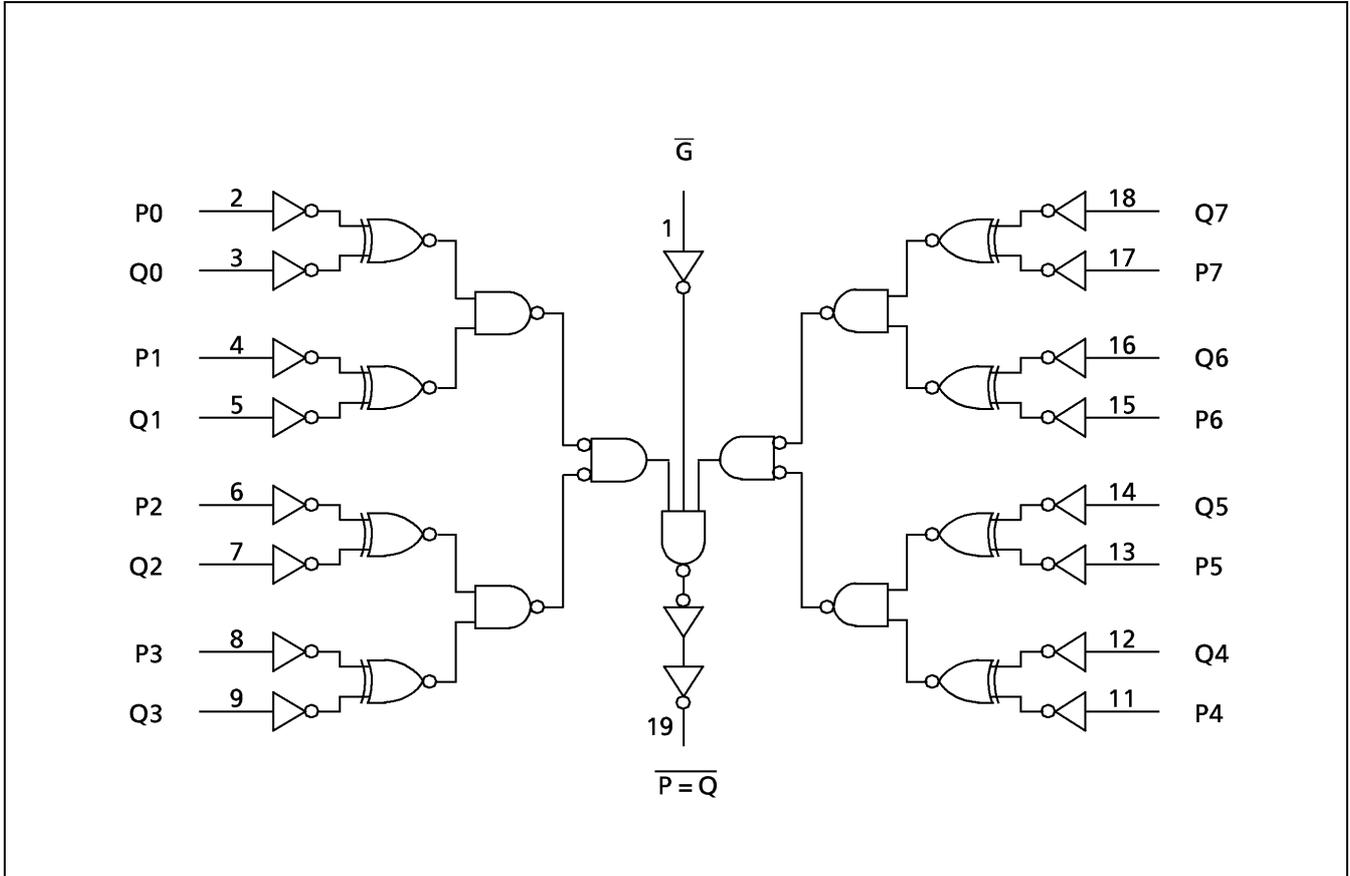
INPUTS		OUTPUT
P, Q	\bar{G}	$\overline{P=Q}$
P = Q	L	L
P ≠ Q	L	H
X	H	H

x: Don't care

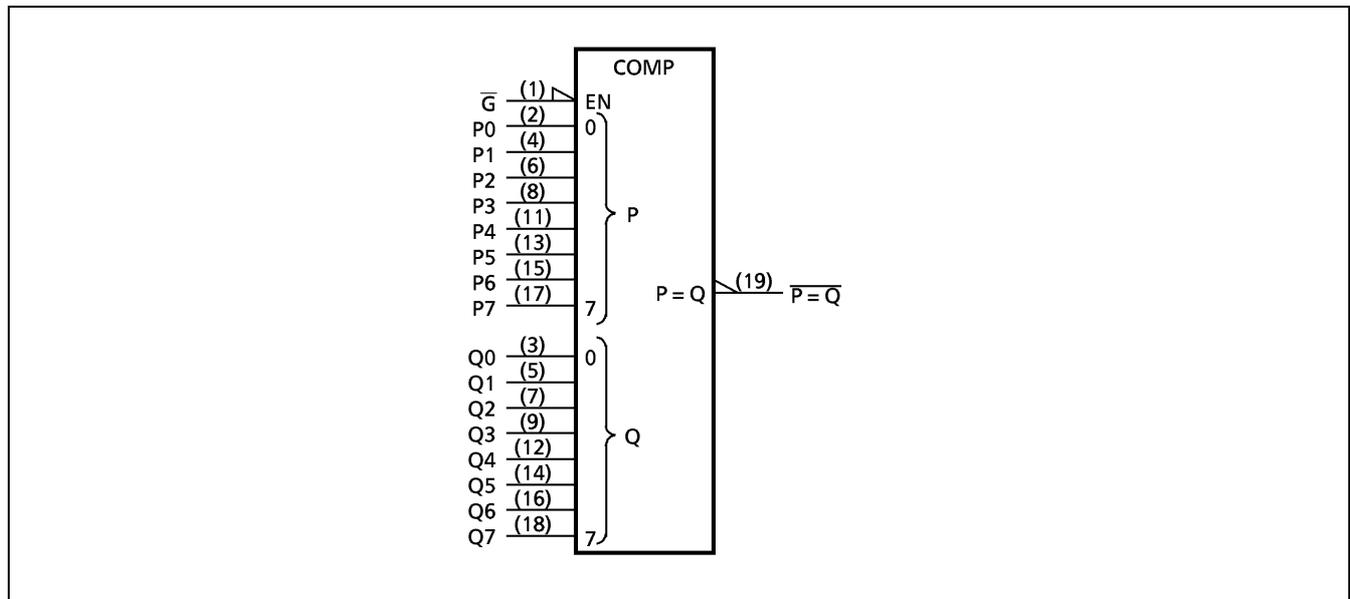
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SYSTEM DIAGRAM



IEC LOGIC SYMBOL



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	4.5~5.5	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~500	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		4.5 } 5.5	2.0	—	—	2.0	—	V	
Low - Level Input Voltage	V_{IL}		4.5 } 5.5	—	—	0.8	—	0.8	V	
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20 \mu\text{A}$	4.5	4.4	4.5	—	4.4	—	V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	—	4.13	—	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20 \mu\text{A}$	4.5	—	0.0	0.1	—	0.1	V
			$I_{OL} = 4 \text{ mA}$	4.5	—	0.17	0.26	—	0.33	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	± 0.1	—	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	4.0	—	40.0		
		I_C	PER INPUT: $V_{IN} = 0.5\text{V}$ or 2.4V OTHER INPUT: V_{CC} or GND	5.5	—	—	2.0	—	2.9	mA

AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	6	12	ns
Propagation Delay Time ($P_n, Q_n - \overline{P=Q}$)	t_{pLH} t_{pHL}		—	17	27	
Propagation Delay Time ($\overline{G} - \overline{P=Q}$)	t_{pLH} t_{pHL}		—	12	19	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40\sim 85^\circ\text{C}$		UNIT
			$V_{CC}(\text{V})$	MIN.	TYP.	MAX.	MIN.	
Output Transition Time	t_{TLH}		4.5	—	8	15	—	ns
	t_{THL}		5.5	—	7	13	—	
Propagation Delay Time ($P_n, Q_n - \overline{P=Q}$)	t_{pLH}		4.5	—	21	32	—	ns
	t_{pHL}		5.5	—	18	29	—	
Propagation Delay Time ($\overline{G} - \overline{P=Q}$)	t_{pLH}		4.5	—	15	23	—	ns
	t_{pHL}		5.5	—	13	21	—	
Input Capacitance	C_{IN}		—	5	10	—	10	pF
Power Dissipation Capacitance	$C_{PD} (1)$		—	32	—	—	—	

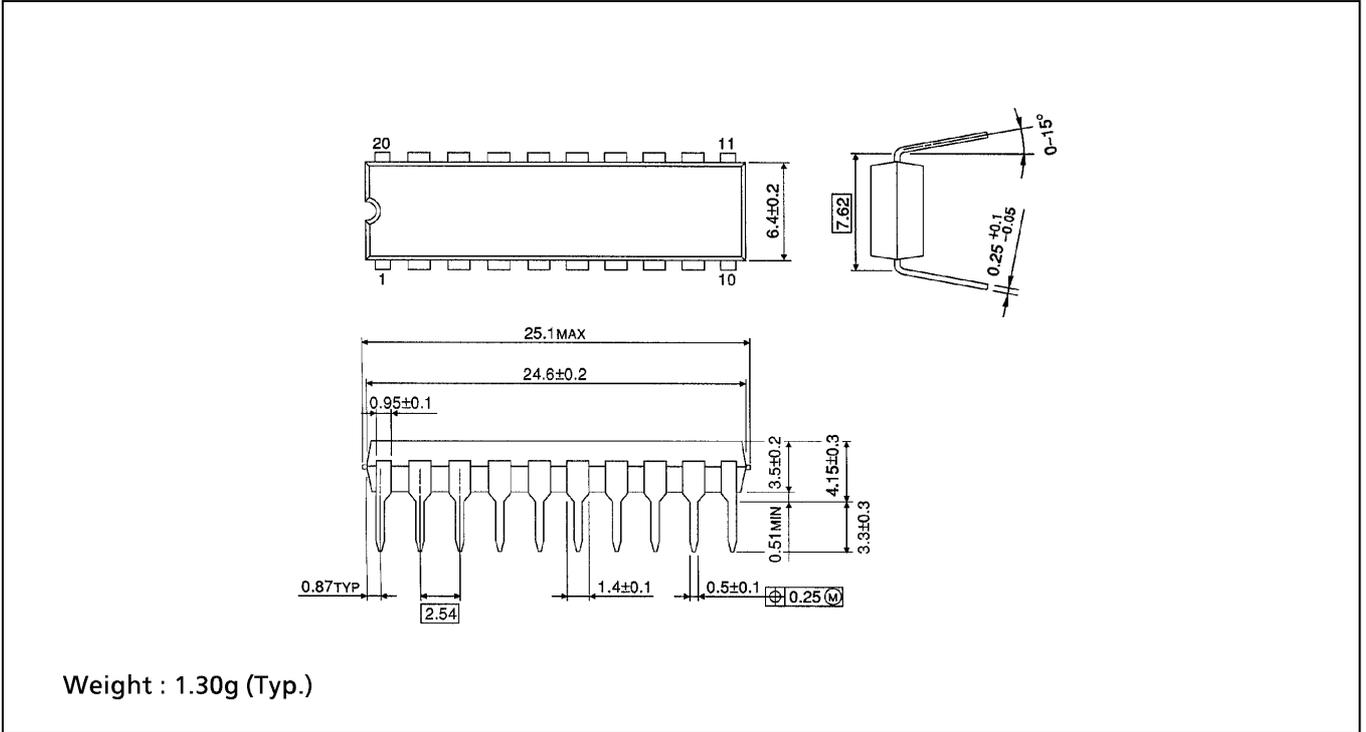
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

Unit in mm



SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

